

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A method of making a semiconductor structure, comprising:  
determining calculating a first polish time, sufficient to planarize a layer on a semiconductor substrate;  
polishing the layer for said first polish time, to planarize the layer; and  
polishing the layer to a predetermined thickness.
2. (Currently Amended) The method of claim 1, further comprising, prior to the calculating determining of said first polish time, measuring the thickness of the layer.
3. (Currently Amended) The method of claim 1, further comprising, prior to the calculating determining of said first polish time, measuring the a pattern density of the layer.
4. (Currently Amended) The method of claim 1, further comprising, prior to the calculating determining of said first polish time, identifying the a composition of the layer.
5. (Original) The method of claim 1, further comprising determining a second polish time sufficient to reduce the thickness of the layer after planarization to the predetermined thickness;  
wherein the polishing of the layer to the predetermined thickness comprises polishing the layer for said second polish time.
6. (Currently Amended) A process for making a plurality of semiconductor structures, comprising  
making each semiconductor structure by the method of claim 1;  
wherein the a Cpk of the process is at least 1.
7. (Currently Amended) A process for making a plurality of semiconductor structures, comprising:  
making each semiconductor structure by the method of claim 5;

wherein the a Cpk of the process is at least 1.

8. (Currently Amended) The process of claim 7, wherein in the making of each semiconductor structure comprises, prior to the calculating determining of said first polish time, measuring the thickness of the layer, the a pattern density of the layer, and identifying the a composition of the layer.

9-11. (Cancelled)

12. (Currently Amended) In a method of making a semiconductor structure, including polishing a layer by chemical mechanical polishing, the improvement comprising determining calculating a first polish time sufficient to make the layer planar; determining a second polish time to reduce the thickness of the planar layer; and polishing for a third polish time equal to the sum of the first and second polish times.

13. (Original) A method of making a semiconductor device, comprising: making a semiconductor structure by the method of claim 1; and forming a semiconductor device from said structure.

14. (Original) A method of making an electronic device, comprising: making a semiconductor device by the method of claim 13; and forming an electronic device, comprising said semiconductor device.

15. (Original) A method of making a semiconductor device, comprising: making a semiconductor structure by the method of claim 5; and forming a semiconductor device from said structure.

16. (Original) A method of making an electronic device, comprising: making a semiconductor device by the method of claim 15; and forming an electronic device, comprising said semiconductor device.

17-23. (Cancelled)

24. (Currently Amended) A method of making a semiconductor structure, comprising:

polishing a layer on a semiconductor substrat with the a system,  
comprising:

a chemical mechanical polishing apparatus; and  
machine readable medium, comprising code, imbedded in the  
machine readable medium, for calculating a first polish time, sufficient to  
planarize a layer on a semiconductor substrate. of claim 23.

- A  
and*
25. (Original) A method of making a semiconductor device, comprising:  
making a semiconductor structure by the method of claim 24; and  
forming a semiconductor device from said structure.
  26. (Original) A method of making an electronic device, comprising:  
making a semiconductor device by the method of claim 25; and  
forming an electronic device, comprising said semiconductor device.